

MAXIMUM RATINGS

Rating	Symbol	BF 371	BF 373	Unit
Collector-Emitter Voltage	V _{CEO}	30	45	Vdc
Collector-Base Voltage	V _{CBO}	40	45	Vdc
Emitter-Base Voltage	V _{EBO}	4.0		Vdc
Collector Current - Continuous	I _C	100		mA _{dc}
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350	2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0	8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	125	°C/W
Thermal Resistance, Junction to Ambient	R _{θJC}	357	°C/W

BF371 BF373

**CASE 29-02, STYLE 2
TO-92 (TO-226AA)**

NPN SILICON

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Type	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I _C = 1.0 mA _{dc} , I _B = 0)	BF371 BF373	V _{(BR)CEO}	30 45	—	—	Vdc
Collector-Base Breakdown Voltage (I _C = 100 μA _{dc} , I _E = 0)	BF371 BF373	V _{(BR)CBO}	40 45	—	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)		V _{(BR)EBO}	4.0	—	—	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)		I _{CBO}	—	—	50	nA _{dc}
ON CHARACTERISTICS						
DC Current Gain (I _C = 7.0 mA _{dc} , V _{CE} = 10 Vdc) (I _C = 20 mA _{dc} , V _{CE} = 2.0 Vdc)		h _{FE}	40 15	— —	— —	—
Collector-Emitter Saturation Voltage (I _C = 20 mA _{dc} , I _B = 2.0 mA _{dc})		V _{CE(sat)}	—	—	0.50	Vdc
Base-Emitter On Voltage (I _C = 7.0 mA, V _{CE} = 10 Vdc)		V _{BE(on)}	—	—	0.90	Vdc
DYNAMIC CHARACTERISTICS						
Current Gain - Bandwidth Product (I _C = 5 mA _{dc} , V _{CE} = 10 Vdc, f = 100 MHz)	BF371 BF373	f _T	400 500	720 720	—	MHz
Common Emitter Feedback Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{re}	—	0.20	0.32	pF